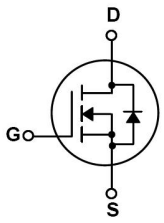
TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

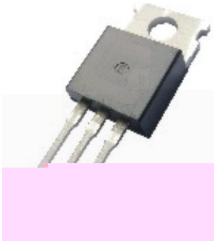
, ,

Low gate charge, low crss, fast switching.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

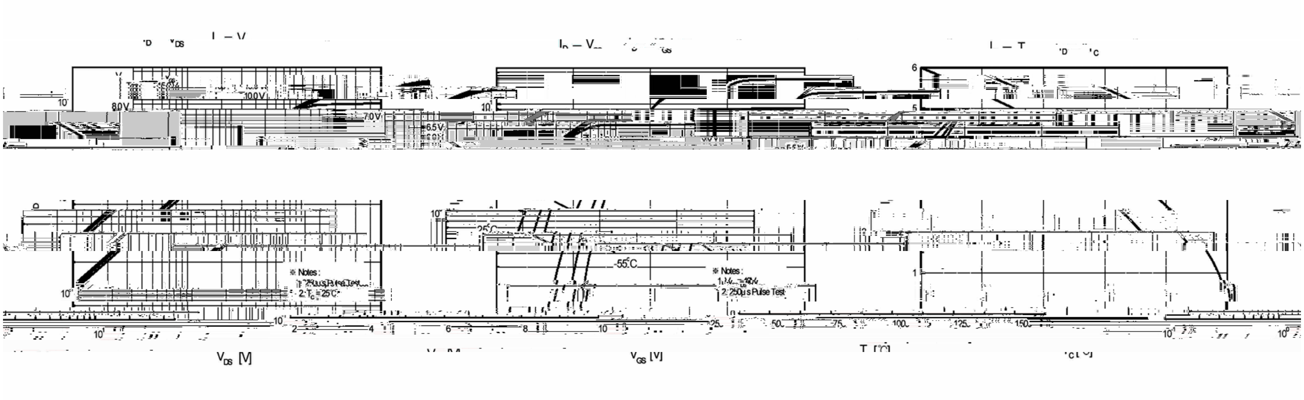


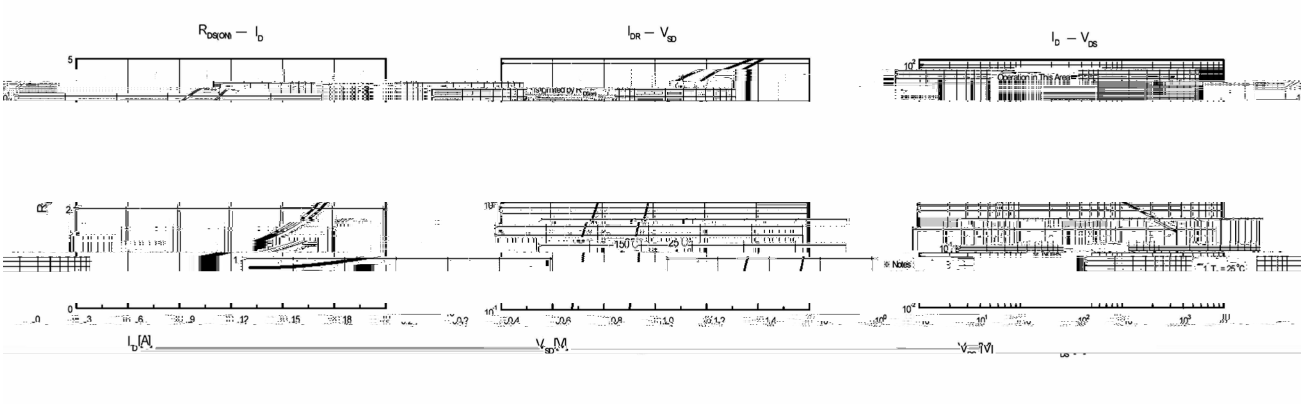



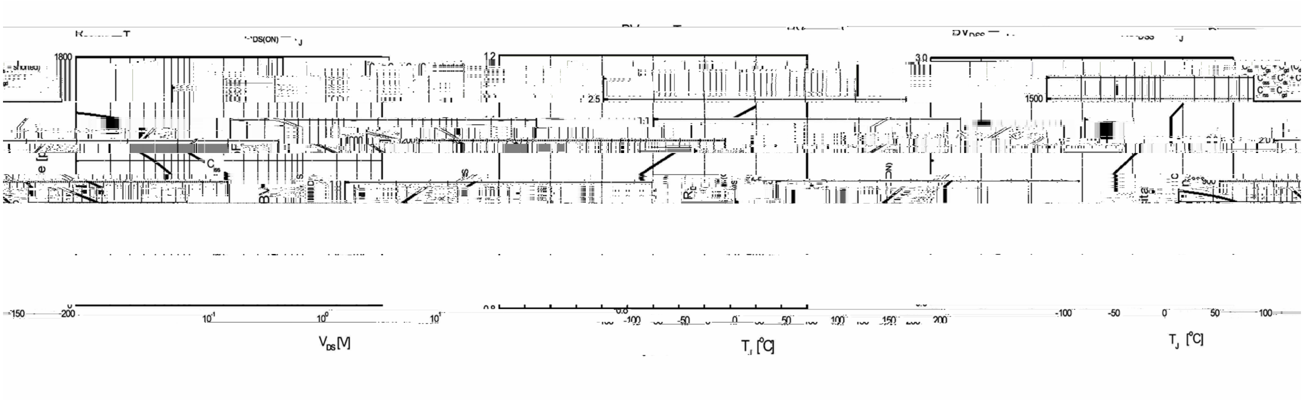
PIN1 G PIN 2 D PIN 3 S

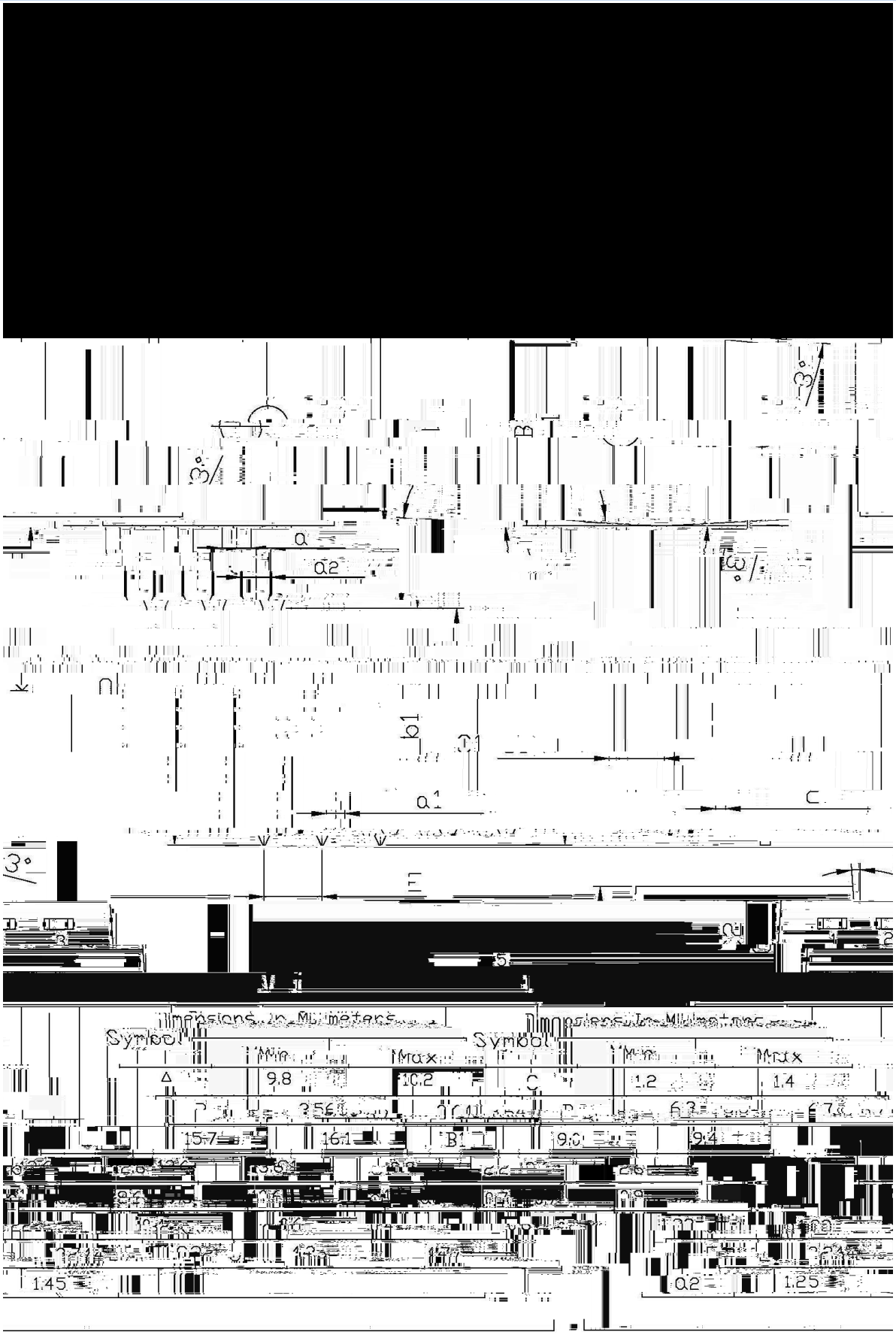
See Marking Instructions.

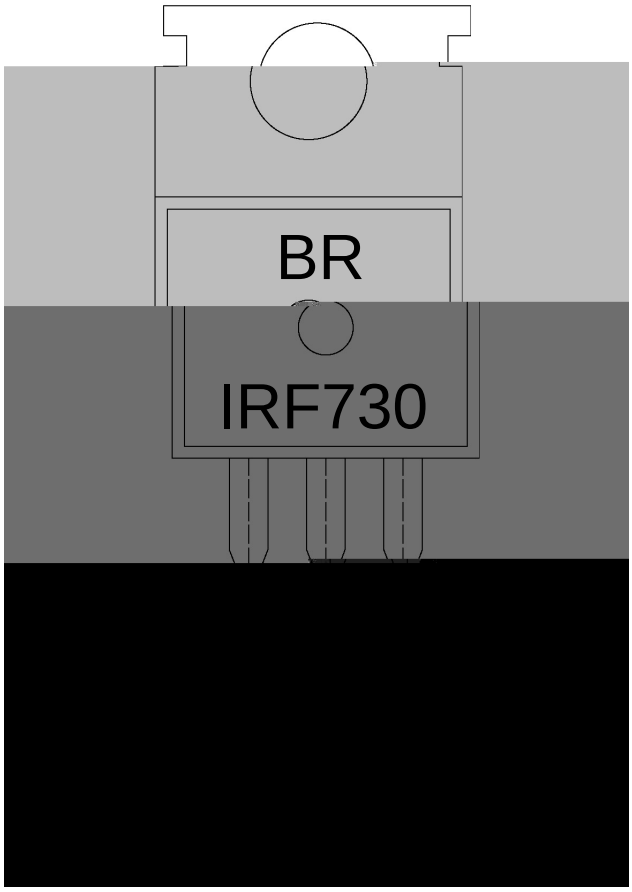
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DSS}$ | 400 | V |
| Drain Current | $I_D$(Tc=25 ) | 6.0 | A |
| | $I_D$(Tc=100 ) | 3.6 | A |
| Pulsed Drain Current | $I_{DM}$ | 24 | A |
| Gate-Source Voltage | $V_{GSS}$ | ±30 | V |
| Avalanche Current | $I_{AR}$ | 5.5 | A |
| Single Pulsed Avalanche Energy | $E_{AS}$ | 390 | mJ |
| Repetitive Avalanche Energy | $E_{AR}$ | 8.75 | mJ |
| Total Power Dissipation | $P_D$(Tc=25 ) | 87.5 | W |
| Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 to 150 | |


$V_{DS}$ [V]
$V_{GS}$ [V]


$R_{DS(ON)}$ — $I_D$
$I_{DR}$ — $V_{SD}$
$I_D$ — $V_{DS}$
Operation in This Area
$I_D$ [A]
$V_{SD}$ [V]


$V_{DS}$ [V]
$T_J$ [°C]
$T_J$ [°C]


Dimensions In Millimeters
Symbol
Min
Max
9.8
10.2
15.7
16.1
9.0
9.4
1.45
1.25



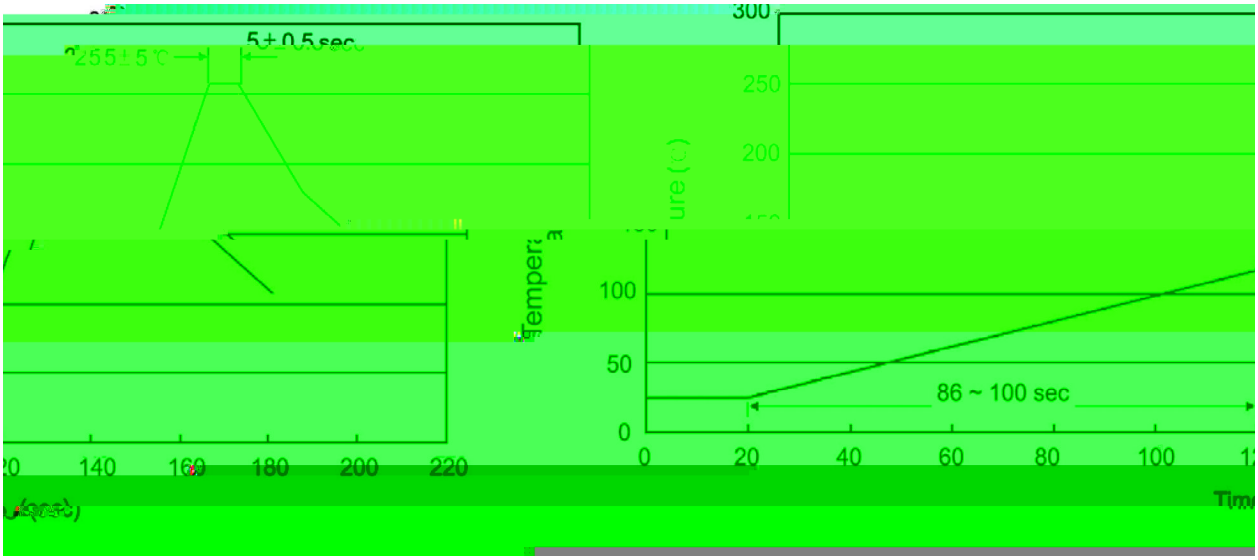

BR

IRF730

****

Note:

| | |
|---|---|
| BR: | Company Code |
| IRF730: | Product Type. |
| ****: | Lot No. Code, code change with Lot No. |




| | | | | | | | |
|---|---|---|---|---|---|---|---|
| | | | | | | Note: | |
| 1 | | 25 | 150 | | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | | 255±5 | | | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

| | | | |
|---|---|---|---|
| 270±5 | 10±1 sec. | Temp.:270±5 | Time:10±1 sec |

/ BULK

Package Type